

# Introduction to CMOS VLSI Design

## Elementary Logic Design

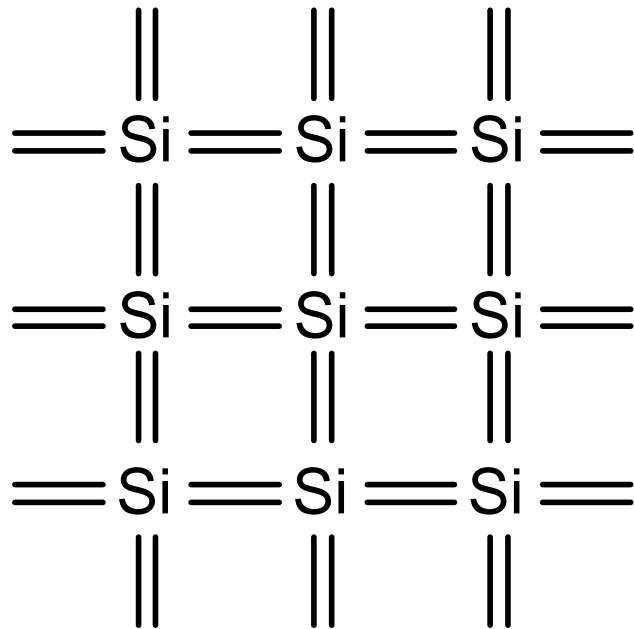
# Introduction

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- ❑ Integrated circuits: many transistors on one chip.
- ❑ *Very Large Scale Integration (VLSI)*: very many
- ❑ *Complementary Metal Oxide Semiconductor*
  - Fast, cheap, low power transistors
- ❑ Today: How to build your own simple CMOS chip
  - CMOS transistors
  - Building logic gates from transistors
  - Transistor layout and fabrication
- ❑ Rest of the course: How to build a good CMOS chip

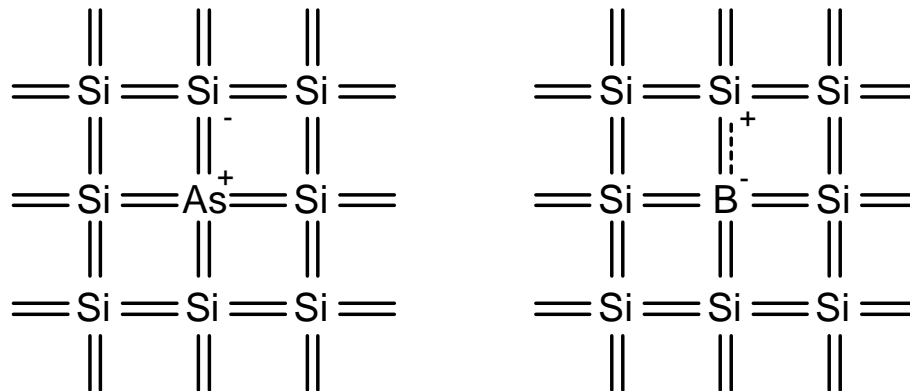
# Silicon Lattice

- ❑ Transistors are built on a silicon substrate
- ❑ Silicon is a Group IV material
- ❑ Forms crystal lattice with bonds to four neighbors



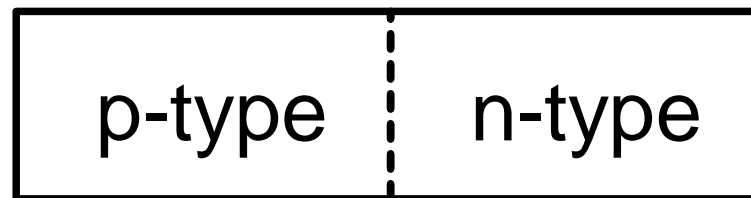
# Dopants

- ❑ Silicon is a semiconductor
- ❑ Pure silicon has no free carriers and conducts poorly
- ❑ Adding dopants increases the conductivity
- ❑ Group V: extra electron (n-type)
- ❑ Group III: missing electron, called hole (p-type)



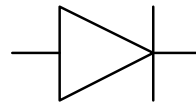
# p-n Junctions

- ❑ A junction between p-type and n-type semiconductor forms a diode.
- ❑ Current flows only in one direction



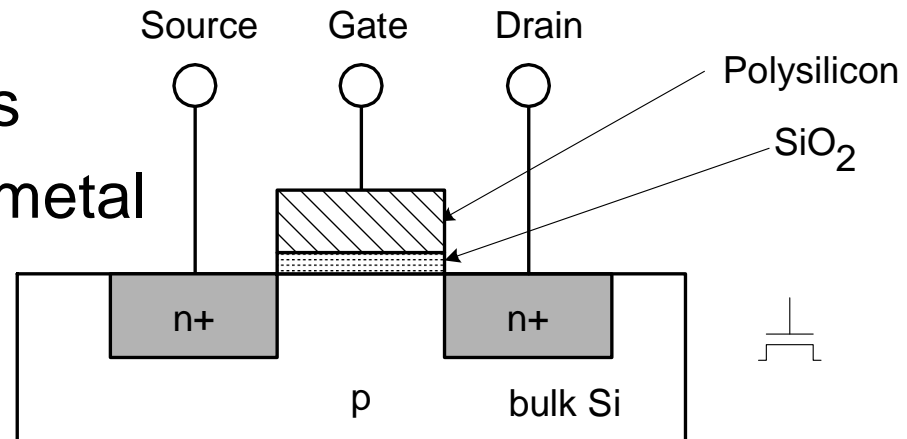
anode

cathode



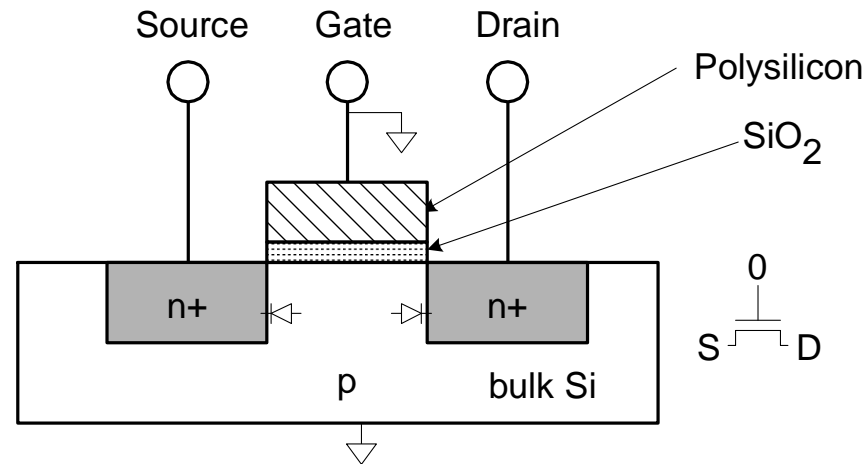
# nMOS Transistor

- ❑ Four terminals: gate, source, drain, body
- ❑ Gate – oxide – body stack looks like a capacitor
  - Gate and body are conductors
  - $\text{SiO}_2$  (oxide) is a very good insulator
  - Called metal – oxide – semiconductor (MOS) capacitor
  - Even though gate is no longer made of metal



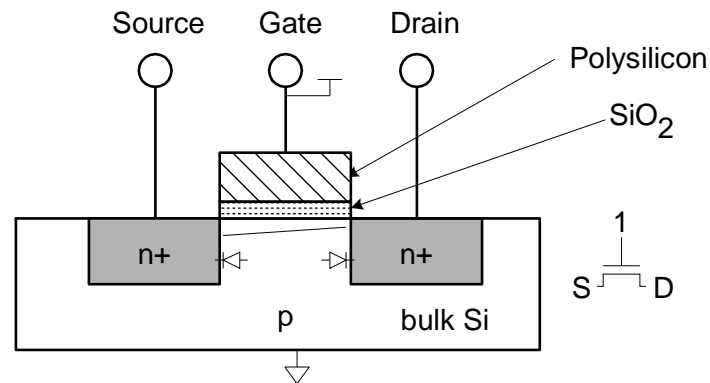
# nMOS Operation

- ❑ Body is commonly tied to ground (0 V)
- ❑ When the gate is at a low voltage:
  - P-type body is at low voltage
  - Source-body and drain-body diodes are OFF
  - No current flows, transistor is OFF



# nMOS Operation Cont.

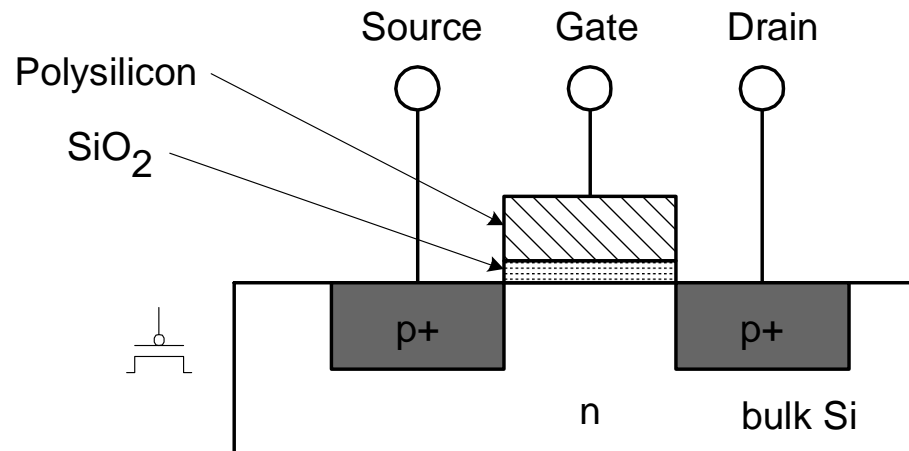
- When the gate is at a high voltage:
  - Positive charge on gate of MOS capacitor
  - Negative charge attracted to body
  - Inverts a channel under gate to n-type
  - Now current can flow through n-type silicon from source through channel to drain, transistor is ON





# pMOS Transistor

- ❑ Similar, but doping and voltages reversed
  - Body tied to high voltage ( $V_{DD}$ )
  - Gate low: transistor ON
  - Gate high: transistor OFF
  - Bubble indicates inverted behavior

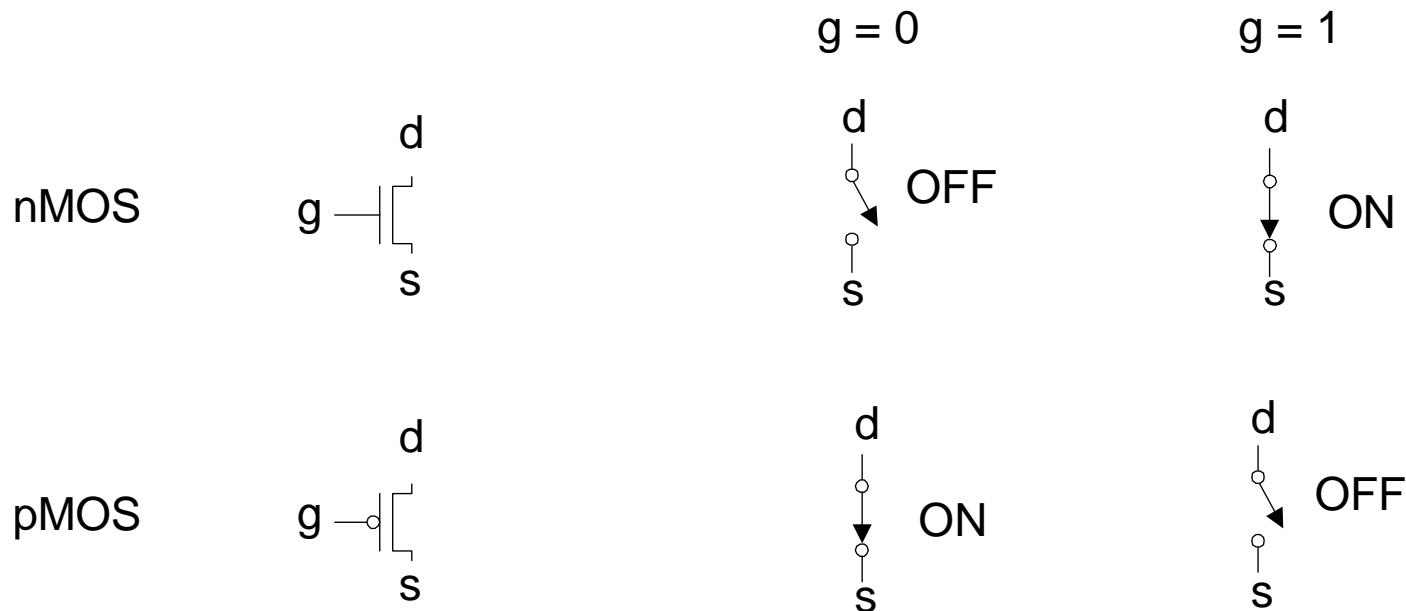


# Power Supply Voltage

- ❑ GND = 0 V
- ❑ In 1980's,  $V_{DD} = 5V$
- ❑  $V_{DD}$  has decreased in modern processes
  - High  $V_{DD}$  would damage modern tiny transistors
  - Lower  $V_{DD}$  saves power
- ❑  $V_{DD} = 3.3, 2.5, 1.8, 1.5, 1.2, 1.0, \dots$

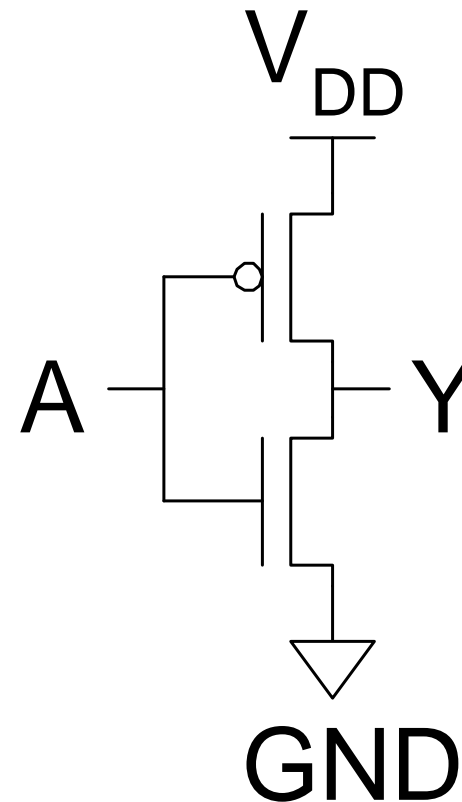
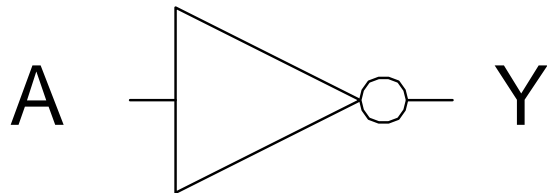
# Transistors as Switches

- ❑ We can view MOS transistors as electrically controlled switches
- ❑ Voltage at gate controls path from source to drain



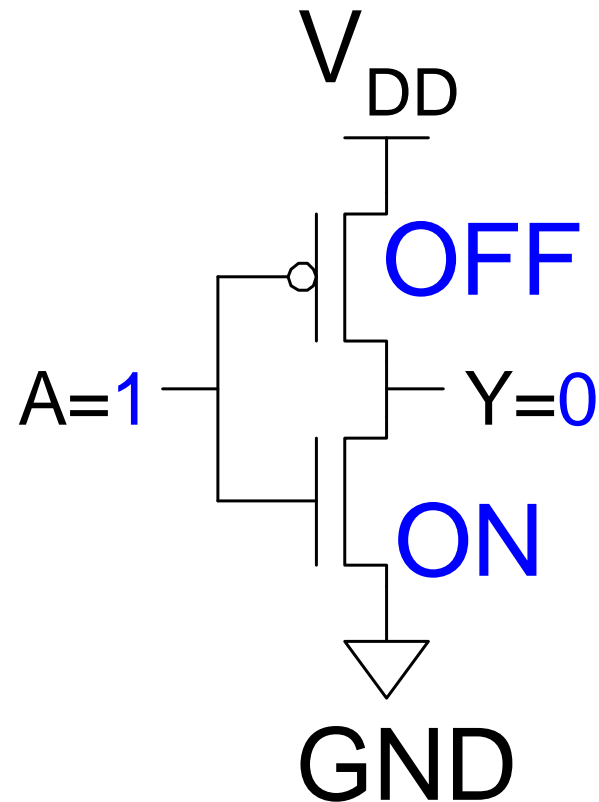
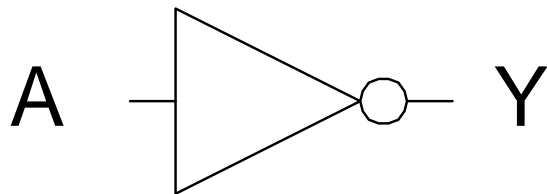
# CMOS Inverter

A	Y
0	
1	



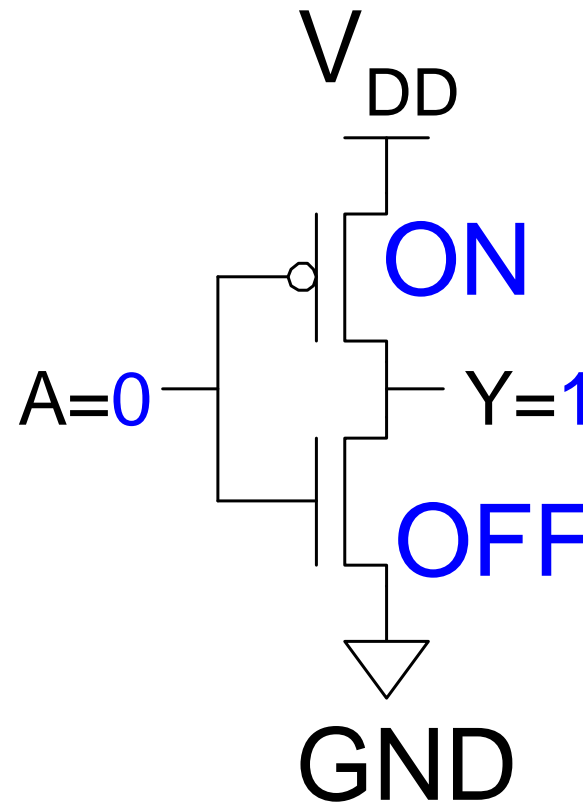
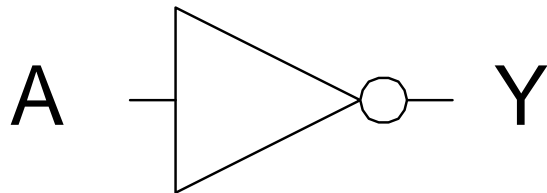
# CMOS Inverter

A	Y
0	
1	0



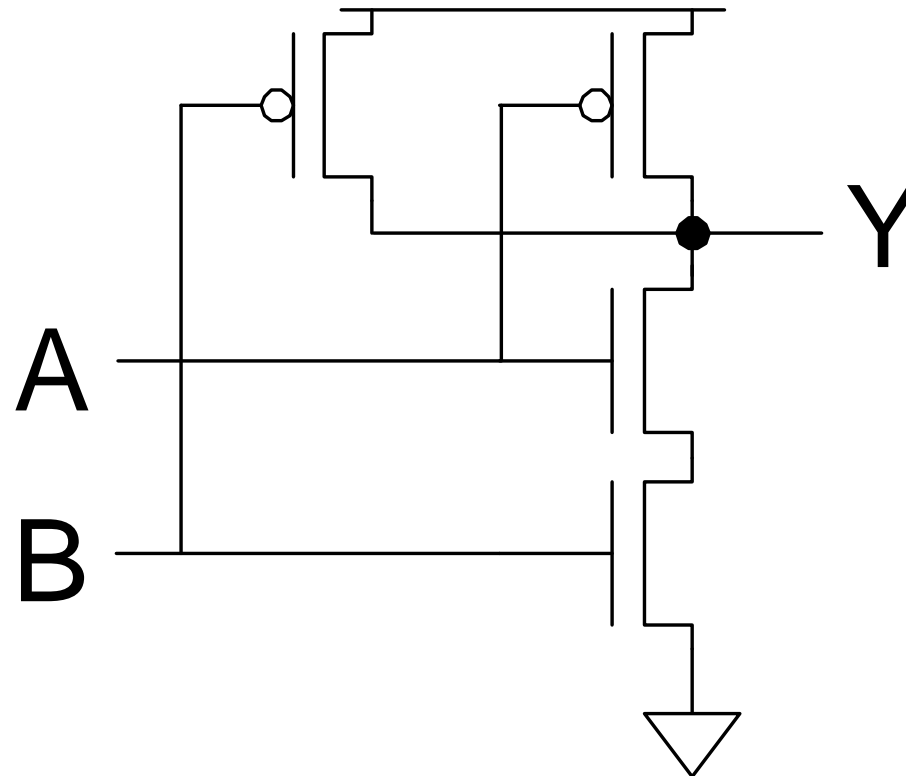
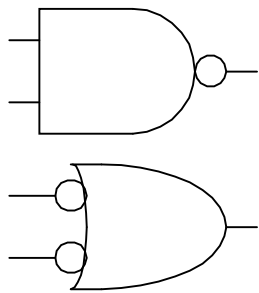
# CMOS Inverter

A	Y
0	1
1	0



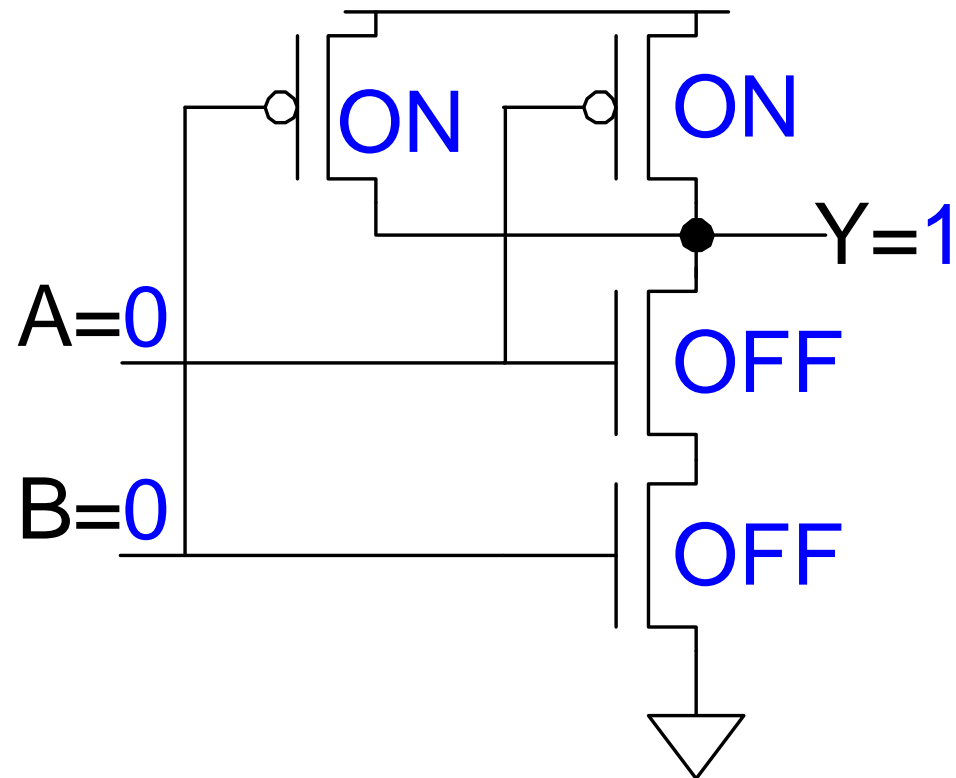
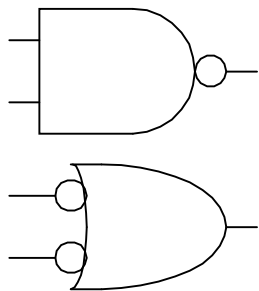
# CMOS NAND Gate

A	B	Y
0	0	
0	1	
1	0	
1	1	



# CMOS NAND Gate

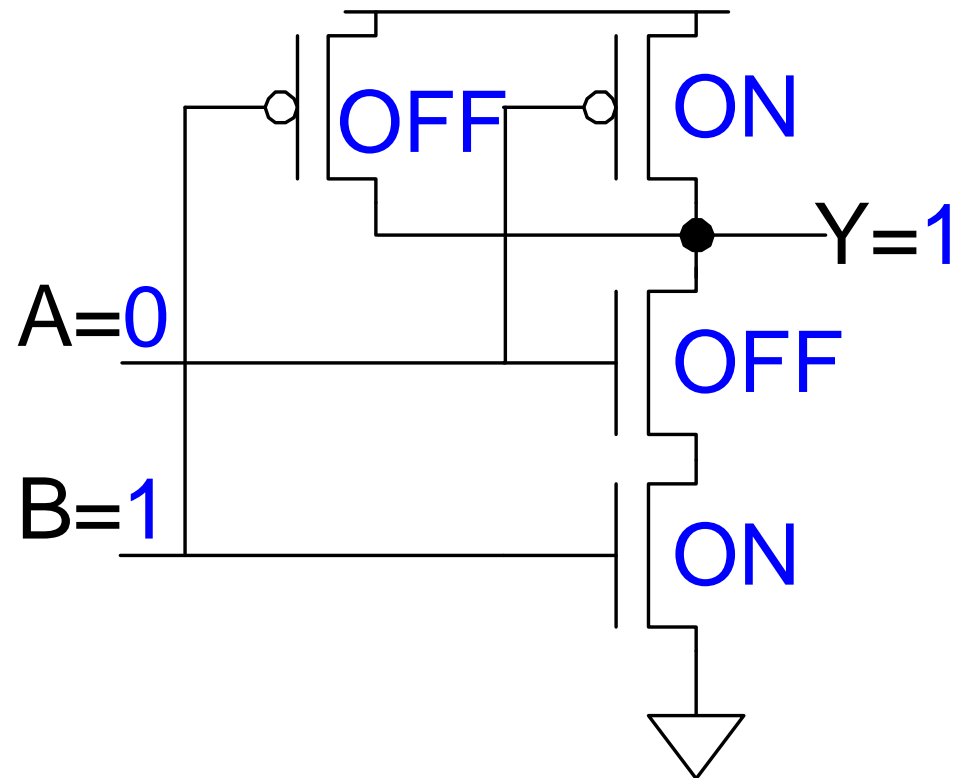
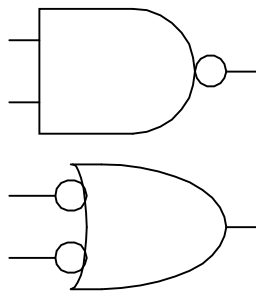
A	B	Y
<b>0</b>	<b>0</b>	<b>1</b>
0	1	
1	0	
1	1	





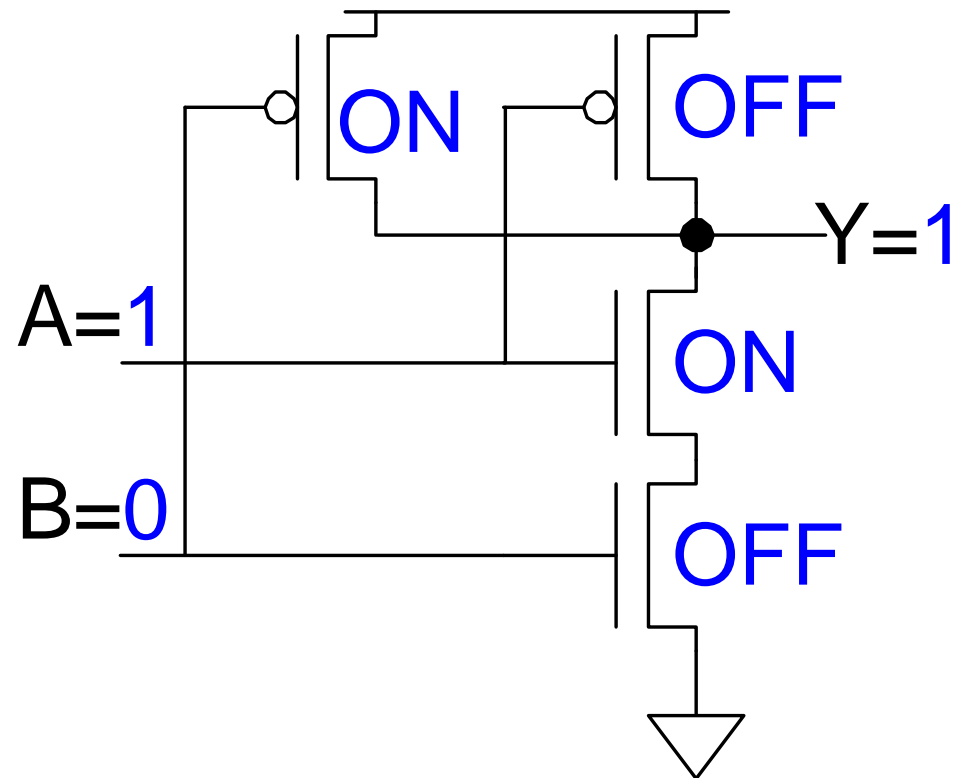
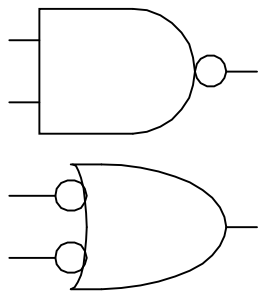
# CMOS NAND Gate

A	B	Y
0	0	1
<b>0</b>	<b>1</b>	<b>1</b>
1	0	
1	1	



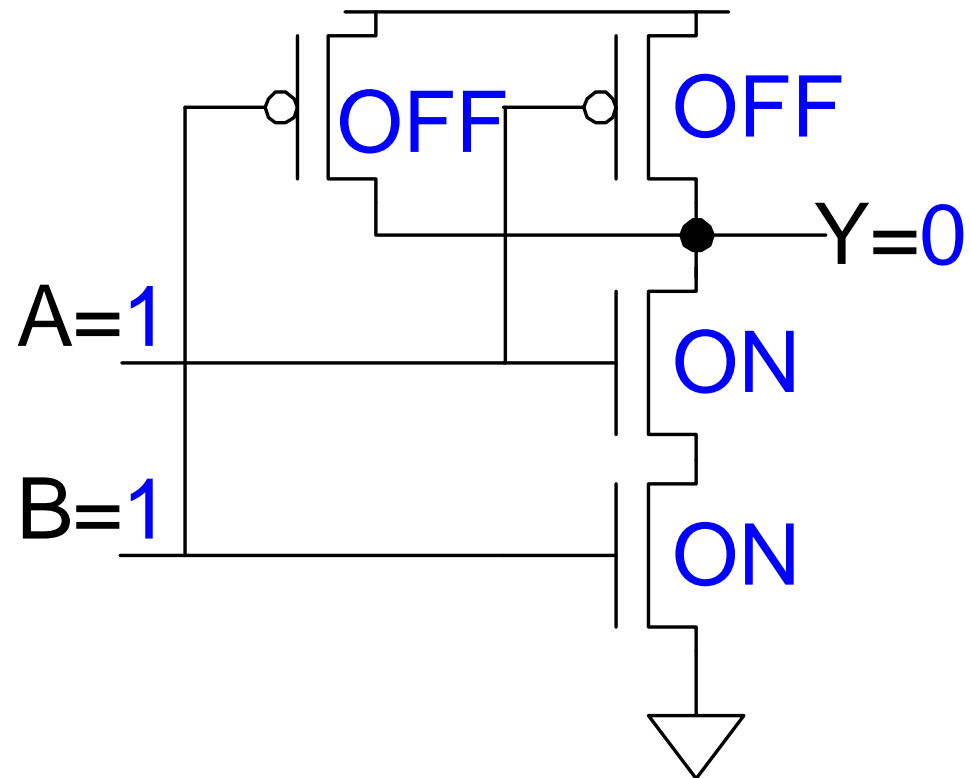
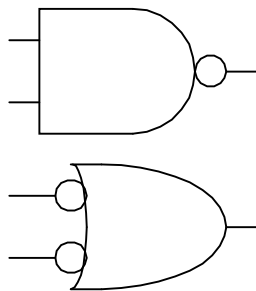
# CMOS NAND Gate

A	B	Y
0	0	1
0	1	1
<b>1</b>	<b>0</b>	<b>1</b>
1	1	



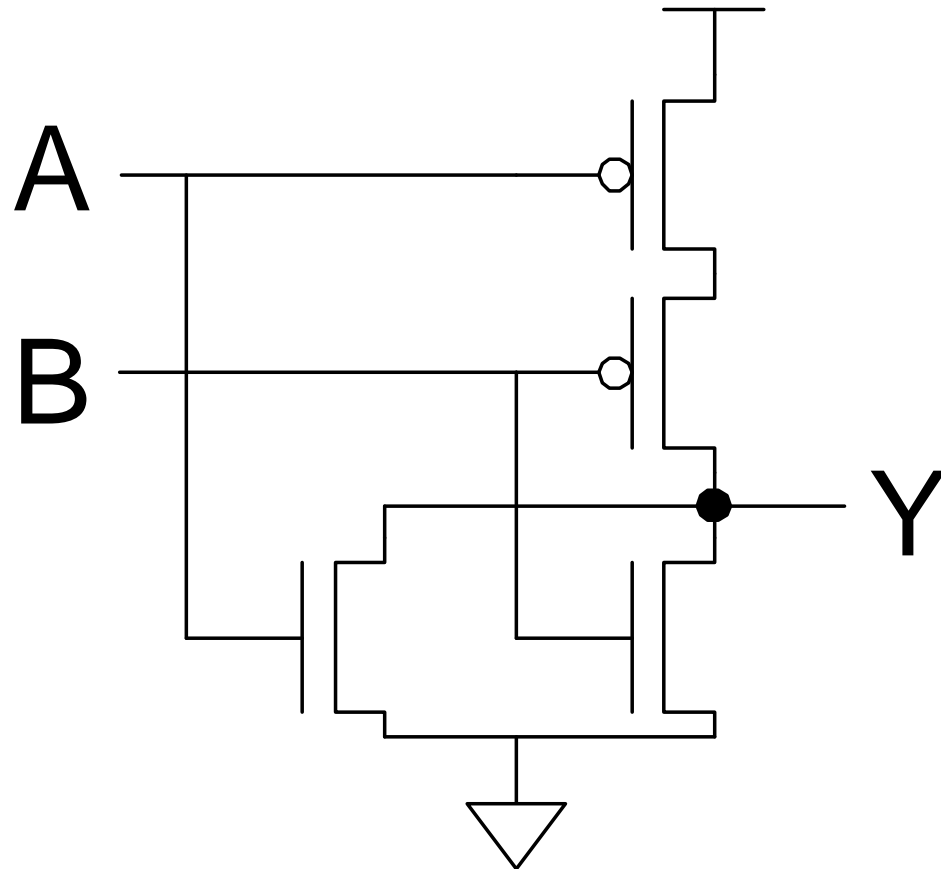
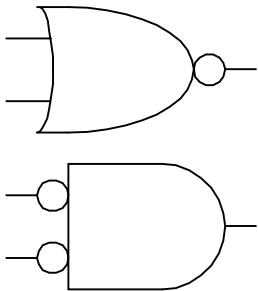
# CMOS NAND Gate

A	B	Y
0	0	1
0	1	1
1	0	1
<b>1</b>	<b>1</b>	<b>0</b>



# CMOS NOR Gate

A	B	Y
0	0	1
0	1	0
1	0	0
1	1	0



# 3-input NAND Gate

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- Y pulls low if ALL inputs are 1
- Y pulls high if ANY input is 0

# 3-input NAND Gate

- ❑ Y pulls low if ALL inputs are 1
- ❑ Y pulls high if ANY input is 0

